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CJC

Docket No.: M4065.1019/P1019
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Letters Patent of:
Joseph F. Brooks

Patent No.: 7,098,068

Issued: August 29, 2006

For: METHOD OF FORMING A
CHALCOGENIDE MATERIAL
CONTAINING DEVICE

**Certificate
of Correction**
OCT 1-0 2006

**REQUEST FOR CERTIFICATE OF CORRECTION
PURSUANT TO 37 CFR 1.322**

Attention: Certificate of Correction Branch
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Upon reviewing the above-identified patent, Patentee noted omissions and typographical errors which should be corrected.

In the Claims, the PTO made the following omissions of text to be corrected:

Claim 42, column 10, line 32, "a layer" should read --a first layer--;

Claim 42, column 10, line 34, "the layer" should read --the first layer--; and

Claim 42, column 10, line 49, "Ge_xSe_{100-x}" should read --Ge_xSe_{100-x}--.

OCT 12 2006

In the Other Publications portion of the References Cited section, the PTO made the following errors to be corrected:

"Afifi, M.A.; Labib, H.H.; Fouad, A.A.; Electrical & thermal conductivity of the amorphous semiconductor Ge_xSe_{1-x}, Egypt. J. Phys. 17 (1986) 335-342."

Should read

--Afifi, M.A.; Labib, H.H.; Fouad, S.S.; El-Shazly, A.A., Electrical & thermal conductivity of the amorphous semiconductor Ge_xSe_{1-x}, Egypt. J. Phys. 17 (1986) 335-342.--;

"Fischer-Colbrie, A.; Bienenstock, A.; Fuoss, P.H.; Marcus, M.A., Structure and bonding in photodiffuses amorphous Ag-GeSe₂ thin films, Phys. Rev. B 38 (1988) 12388-12403."

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"Mitkiva, M.; Kozicki, M.N., Silver incorporation in Ge-Se glasses used in programmable metallization cell devices, J. Non-Cryst. Solids 299-302 (2002) 1023-1027."

Should read

--Mitkova, M.; Kozicki, M.N., Silver incorporation in Ge-Se glasses used in programmable metallization cell devices, J. Non-Cryst. Solids 299-302 (2002) 1023-1027.--.

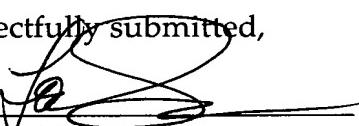
OCT 12 2006

The errors were not in the application as filed or amended by Applicant; accordingly no fee is required.

Transmitted herewith is a proposed Certificate of Correction effecting such amendment. Patentee respectfully solicits the granting of the requested Certificate of Correction.

Dated: October 5, 2006

Respectfully submitted,

By 
Thomas J. D'Amico

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**UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION**

Page 1 of 2

PATENT NO. : 7,098,068
 APPLICATION NO. : 10/796,109
 ISSUE DATE : August 29, 2006
 INVENTORS : Joseph F. Brooks

It is certified that errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In the Claims, the following omissions are corrected:

Claim 42, column 10, line 32, "a layer" should read --a first layer--;

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 1825 Eye Street, NW
 Washington, DC 20006-5403

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